

2024 IEEE 11th Workshop on Wide Bandgap Power Devices & Applications (WiPDA 2024)

**Dayton, Ohio, USA
4-6 November 2024**



**IEEE Catalog Number: CFP24WBP-POD
ISBN: 979-8-3503-7561-9**

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IEEE Catalog Number:	CFP24WBP-POD
ISBN (Print-On-Demand):	979-8-3503-7561-9
ISBN (Online):	979-8-3503-7560-2
ISSN:	2641-8274

Additional Copies of This Publication Are Available From:

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